

ABSTRACT OF THE DISCLOSURE SN #09398189

In a method for fabricating a semiconductor device, a silicide material is formed at least on the surface of an area to be silicided. Then, a first RTA (Rapid Thermal Annealing) process is performed to form a first-reacted silicide region. Next, a supplemental silicon layer is formed over the entire surface; and a second RTA process is performed to form a second-reacted silicide region.

09398189-091799